

Bipolar Transistor

50 V, 10 A, Low V_{CE}(sat), NPN TO-220F-3FS

2SC6144SG

Features

- Adoption of MBIT Process
- Large Current Capacitance (I_C = 10 A)
- Low Collector-to-Emitter Saturation Voltage (V_{CE}(sat) = 180 mV(typ.))
- High-speed Switching ($t_f = 25 \text{ ns(typ.)}$)

Applications

• Relay Drivers, Lamp Drivers, Motor Drivers

Specifications

ABSOLUTE MAXIMUM RATINGS at Ta = 25°C

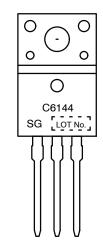
Parameter	Symbol	Conditions	Ratings	Units
Collector-to-Base Voltage	V _{CBO}		60	٧
Collector-to-Emitter Voltage	V _{CEO}		50	٧
Emitter-to-Base Voltage	V _{EBO}		5	V
Collector Current	Ic		10	Α
Collector Current (Pulse)	I _{CP}		13	Α
Base Current	Ι _Β		2	Α
Collector Dissipation	P _C	$T_C = 25^{\circ}C$, $P_T \le 1 \text{ s}$	25	W
Junction Temperature	Tj		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

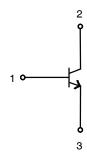
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MARKING DIAGRAM



ELECTRICAL CONNECTION



ORDERING INFORMATION

Device	Package	Shipping
2SC6144SG	TO-220F-3FS (Pb-Free)	50 Units / Tube

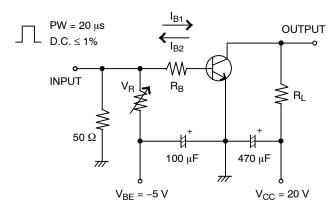
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ELECTRICAL CHARACTERISTICS at Ta = 25°C

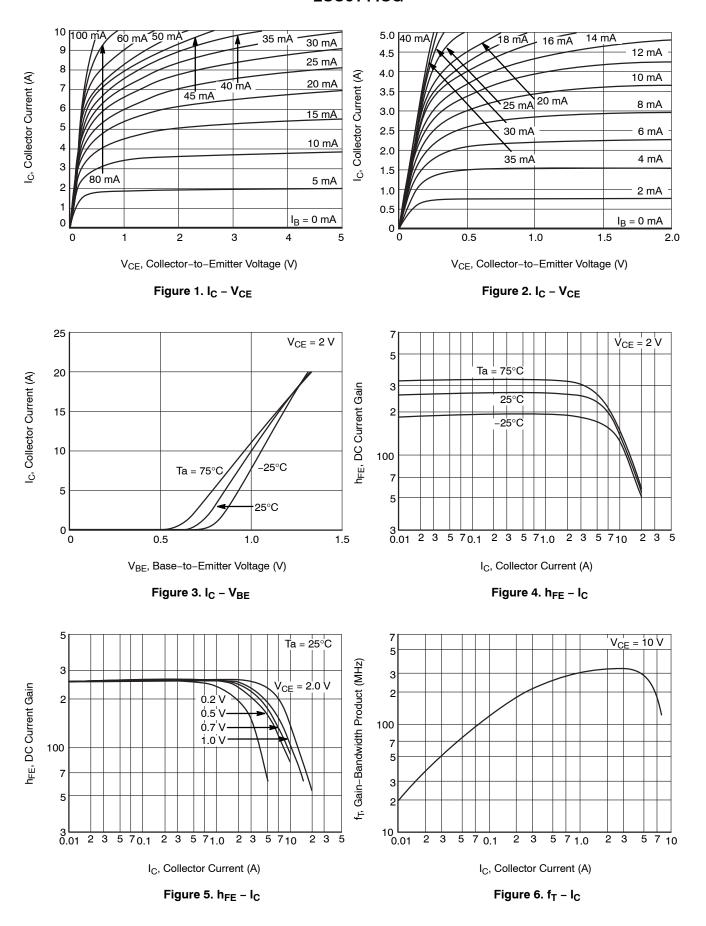
				Ratings		
Parameter	Symbol	Conditions	Min	Тур	Max	Units
Collector Cutoff Current	I _{CBO}	V _{CB} = 40 V, I _E = 0 A	-	-	10	μΑ
Emitter Cutoff Current	I _{EBO}	V _{EB} = 4 V, I _C = 0 A	-	-	10	μΑ
DC Current Gain	h _{FE}	V _{CE} = 2 V, I _C = 270 mA	200	-	560	
Gain-Bandwidth Product	f _T	V _{CE} = 10 V, I _C = 3 A	-	330	_	MHz
Output Capacitance	Cob	V _{CB} = 10 V, f = 1 MHz	-	60	_	pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C = 6 A, I _B = 300 mA	-	180	360	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C = 6 A, I _B = 300 mA	-	-	1.2	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	$I_C = 100 \mu A, I_E = 0 A$	60	-	_	V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 1 mA, R _{BE} = ∞	50	-	_	V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	$I_E = 100 \mu A, I_C = 0 A$	5	-	_	V
Turn-On Time	t _{ON}	See specified Test Circuit.	-	62	_	ns
Storage Time	t _{stg}		_	350	-	ns
Fall Time	t _f		-	25	_	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit



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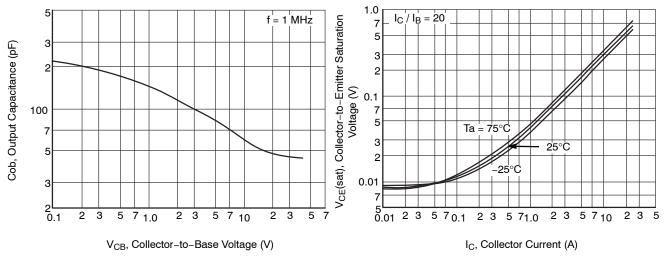


Figure 7. Cob - V_{CB}

Figure 8. V_{CE}(sat) - I_C

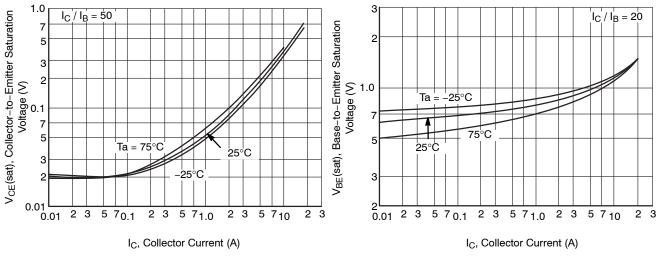


Figure 9. V_{CE}(sat) - I_C

Figure 10. V_{BE}(sat) - I_C

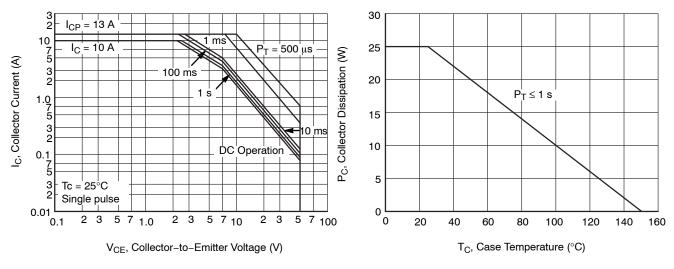


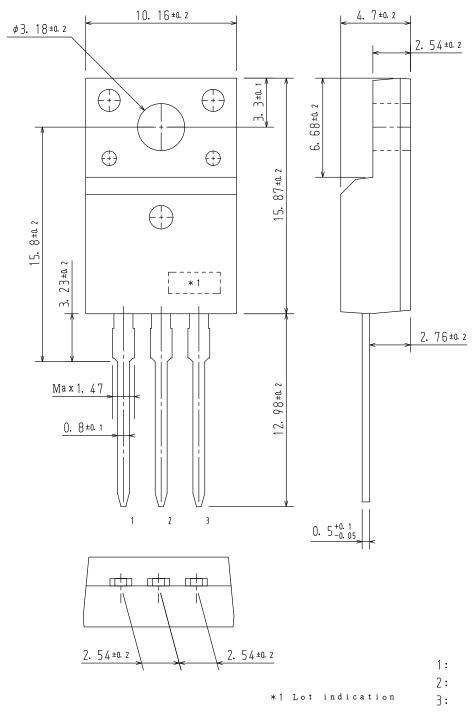
Figure 11. Forward Bias ASO

Figure 12. P_C - T_C



TO-220F-3FS CASE 221AM ISSUE O

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